



Model 325-FF-02 series Bare Die (Flip chip form, Au Pad)

Typical Optical-Electrical Characteristics

 $(I_{F}=20mA, T_{a}=25^{\circ}C)$

ltem	Symbol	Unit	325-FF-02-C		
			Min	Тур	Max
Peak Wavelength	λ _ρ	nm	320	325	330
Radiant Flux	Po	mW	-	3.5	-
Full Width at Half Maximum	⊿λ	nm	-	13	-
Forward Voltage	V _F	V	-	4.9	-

(*)Peak Wavelength Measurement tolerance is ±3nm.

(**)Radiant Flux Measurement tolerance is ±10%.

Binning is available.

Specification and dimension are subject to change for improvement without notice.

$(I_F = 50 \text{mA}, T_a = 25^{\circ}\text{C})$

ltem	Symbol	Unit	325-FF-02-C		
			Min	Тур	Max
Peak Wavelength	λ _p	nm	320	325	330
Radiant Flux	Po	mW	-	8.7	-
Full Width at Half Maximum	⊿λ	nm	-	13	-
Forward Voltage	V _F	V	-	5.2	-

(*)Peak Wavelength Measurement tolerance is ±3nm.

(**)Radiant Flux Measurement tolerance is ±10%.

Binning is available.

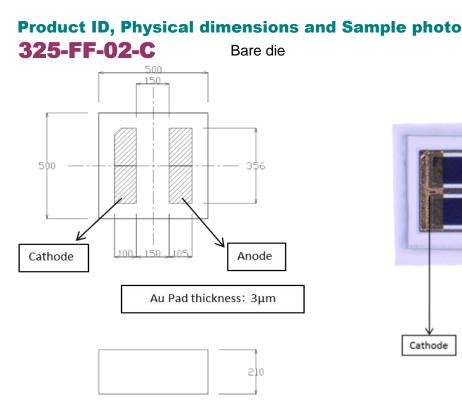
Specification and dimension are subject to change for improvement without notice.

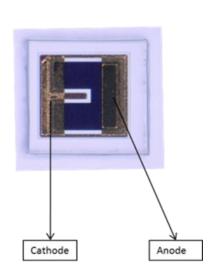




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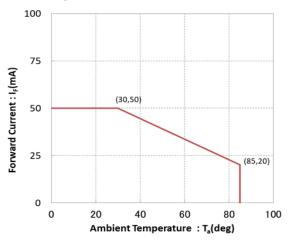




Absolute Maximum Ratings

ltem	Symbol	Unit	Value
Forward Current	I _F	mA	50
Junction Temperature	TJ	°C	90
Operating Temperature	T _{OPR}	°C	-30 ~ +85
Storage Temperature	T _{STR}	°C	-40 \sim +85 (No condensation)

Derating Curve



Notes:

Maximum ratings and derating curve strongly depend on assembly materials.

The above ratings and derating curve were determined using AIN submount ,AI substrate and heatsink. Ratings may be different for other materials and environment.

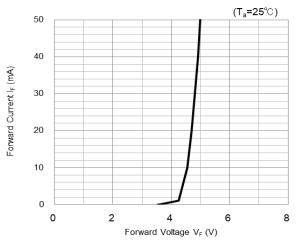


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Reference Data

Forward Voltage vs Forward Current



Forward Current vs Radiated Flux (T_a=25℃) 250 200 Relative Radiant Flux (%) 150 100 50 0 0 10 20 30 40 50 Forward Current I_F (mA)

Spectrum

